

## DC-4GHz Reflective SPDT

### GaAs Monolithic Microwave IC in SMD leadless package

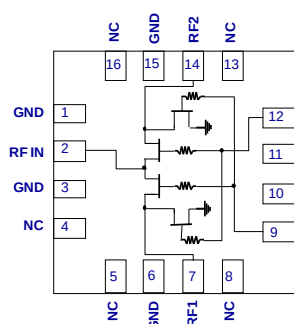
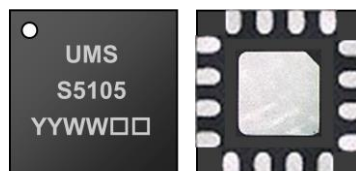
#### Description

The CHS5105-QAG is a monolithic FET based reflective switch.

It is designed for a wide range of applications, from military to commercial systems.

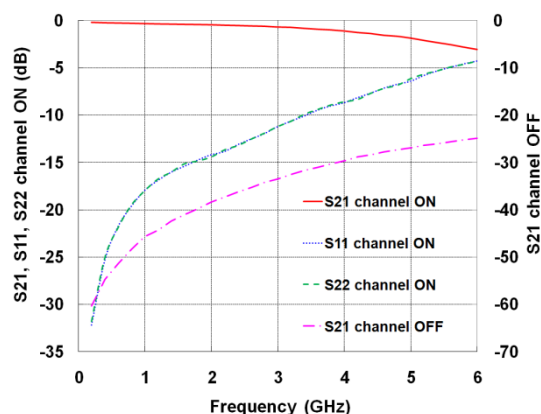
The circuit is manufactured with a pHEMT process, 0.25 $\mu$ m gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied in RoHS compliant SMD package.



#### Main Features

- Broadband performance: DC-4GHz
- Low insertion loss: 0.7dB
- Isolation: 40dB
- Return loss: 16dB
- Input P1dB: 30dBm
- QAG-QFN3x3
- MSL1



#### Main Electrical Characteristics

Tamb.= +25°C

| Symbol | Parameter                         | Min | Typ | Max | Unit |
|--------|-----------------------------------|-----|-----|-----|------|
| Freq   | Frequency range                   | DC  |     | 4   | GHz  |
| IL     | On state insertion loss           |     | 0.7 |     | dB   |
| ISOL   | Off state isolation               |     | 40  |     | dB   |
| RL     | On state return loss              |     | 16  |     | dB   |
| IP1dB  | Input Power @1dB gain compression |     | 30  |     | dBm  |

**Electrical Characteristics <sup>(1)</sup>**

Tamb.= +25°C, specifications are given for 50Ω source and load impedances.

| Symbol     | Parameter                                         | Condition                                                                                | Min | Typ                  | Max | Unit |
|------------|---------------------------------------------------|------------------------------------------------------------------------------------------|-----|----------------------|-----|------|
| Freq       | Frequency range                                   |                                                                                          | DC  |                      | 4   | GHz  |
| IL         | On state insertion loss <sup>(2)</sup>            | DC - 2GHz<br>DC - 4GHz                                                                   |     | 0.3<br>0.7           |     | dB   |
| ISOL       | Off state isolation                               | DC - 2GHz<br>DC - 4GHz                                                                   |     | 45<br>35             |     | dB   |
| RL         | On state input and output return losses           | DC - 2GHz<br>DC - 4GHz                                                                   |     | 16<br>12             |     | dB   |
| VH         | Control voltage high level                        |                                                                                          |     | 0                    | 0.5 |      |
| VL         | Control voltage low level                         |                                                                                          | -8  | -5                   |     | V    |
| IP1dB      | Input Power @1dB gain compression.                | DC - 1GHz<br>VL=-5V/VH=0V<br>VL=-8V/VH=0V<br>1GHz - 4GHz<br>VL=-5V/VH=0V<br>VL=-8V/VH=0V |     | 27<br>30<br>30<br>33 |     | dBm  |
| Ton / Toff | Switching time                                    | 50% control to 90% RF, and 50% control to 10% RF                                         |     | 10                   |     | ns   |
| Ic         | Current consumption on the control supply voltage | Freq. ≥0.5GHz<br>Pin≤33dBm<br>VH= 0V<br>VL=-5V<br>VL=-8V                                 |     | 150<br>50<br>300     |     | μA   |

<sup>(1)</sup> These values are representative of on-board measurements with correction of the board losses.

<sup>(2)</sup> Variation rate of insertion loss with temperature in the range -40°C to +85°C: 0.002dB/°C

**Absolute Maximum Ratings <sup>(1)</sup>**

Tamb.= +25°C

| Symbol | Parameter                                         | Values      | Unit |
|--------|---------------------------------------------------|-------------|------|
| VH     | High level control voltage                        | 0.8         | V    |
| VL     | Low level control voltage                         | -10         | V    |
| Pin    | Maximum peak input power overdrive <sup>(2)</sup> | 37          | dBm  |
| Tj     | Junction temperature <sup>(3)</sup>               | 175         | °C   |
| Ta     | Operating temperature range                       | -40 to +85  | °C   |
| Tstg   | Storage temperature range                         | -55 to +150 | °C   |

<sup>(1)</sup> Operation of this device above anyone of these parameters may cause permanent damage.

<sup>(2)</sup> Duration < 1s, Frequency >1GHz

<sup>(3)</sup> Thermal Resistance channel to ground paddle <33°C/W for Tamb. = +85°C.

**SPDT truth table**

| PAD A | PAD B | Electrical path RFC to RF1 | Electrical path RFC to RF2 |
|-------|-------|----------------------------|----------------------------|
| VH    | VL    | ON                         | OFF                        |
| VL    | VH    | OFF                        | ON                         |

## Device thermal performances

All the figures given in this section are obtained assuming that the QFN device is cooled down only by conduction through the package thermal pad (no convection mode considered). The temperature is monitored at the package back-side interface (Tcase) as shown below.

The system maximum temperature must be adjusted in order to guarantee that Tcase remains below the maximum value specified in the next table. So, the PCB system must be designed to comply with this requirement.

A derating must be applied on the dissipated power if the Tcase temperature can not be maintained below the maximum temperature specified (see the curve Pdiss. Max.) in order to guarantee the nominal device life time (MTTF).

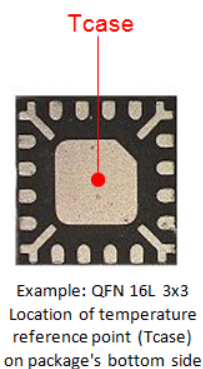
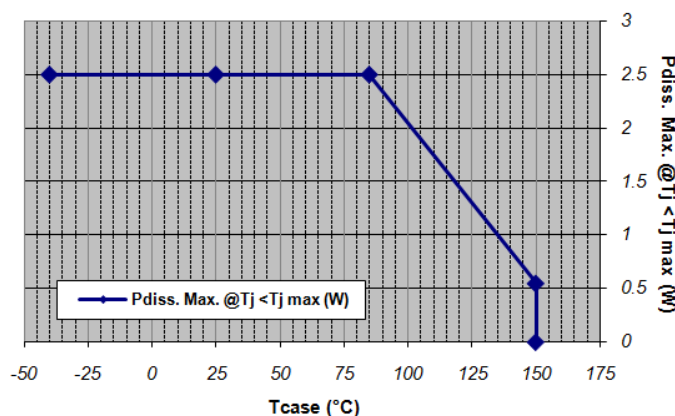
### DEVICE THERMAL SPECIFICATION : CHS5104-QAG

|                                                            |   |          |
|------------------------------------------------------------|---|----------|
| Recommended max. junction temperature (Tj max)             | : | 168 °C   |
| Junction temperature absolute maximum rating               | : | 175 °C   |
| Max. continuous dissipated power (Pdiss. Max.)             | : | 2.5 W    |
| => Pdiss. Max. derating above Tcase <sup>(1)</sup> = 85 °C | : | 30 mW/°C |
| Junction-Case thermal resistance (Rth J-C) <sup>(2)</sup>  | : | <33 °C/W |
| Minimum Tcase operating temperature <sup>(3)</sup>         | : | -40 °C   |
| Maximum Tcase operating temperature <sup>(3)</sup>         | : | 85 °C    |
| Minimum storage temperature                                | : | -55 °C   |
| Maximum storage temperature                                | : | 150 °C   |

(1) Derating at junction temperature constant = Tj max.

(2) Rth J-C is calculated for a worst case considering the **hottest junction** of the MMIC and all the devices biased.

(3) Tcase=Package back side temperature measured under the die-attach-pad (see the drawing below).

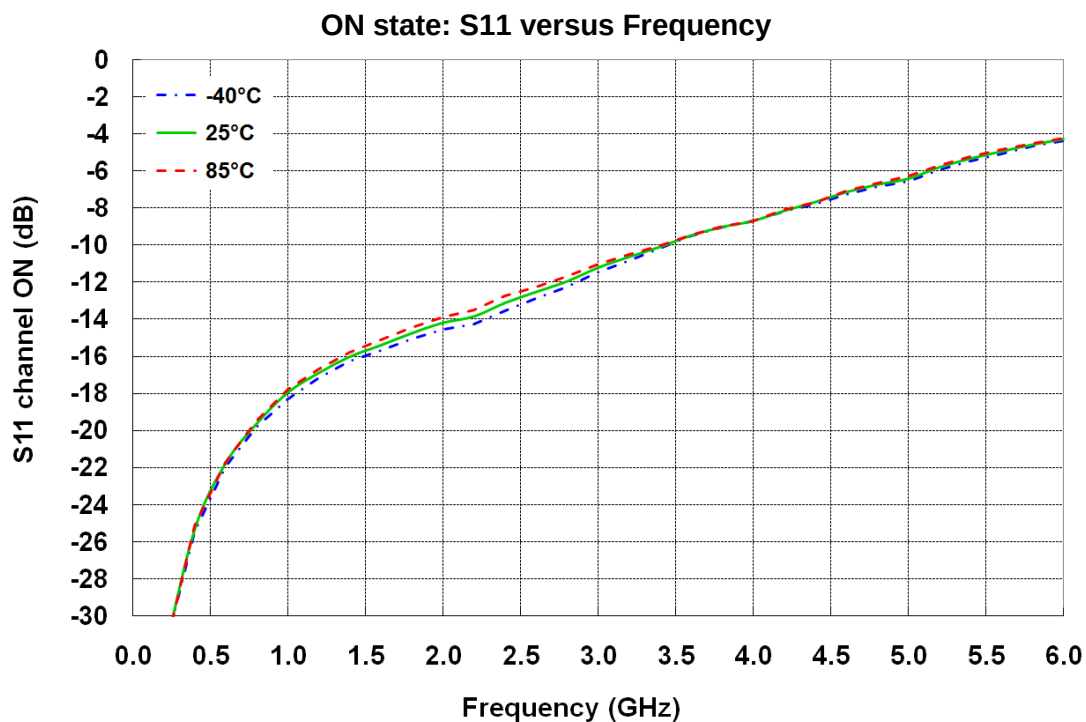
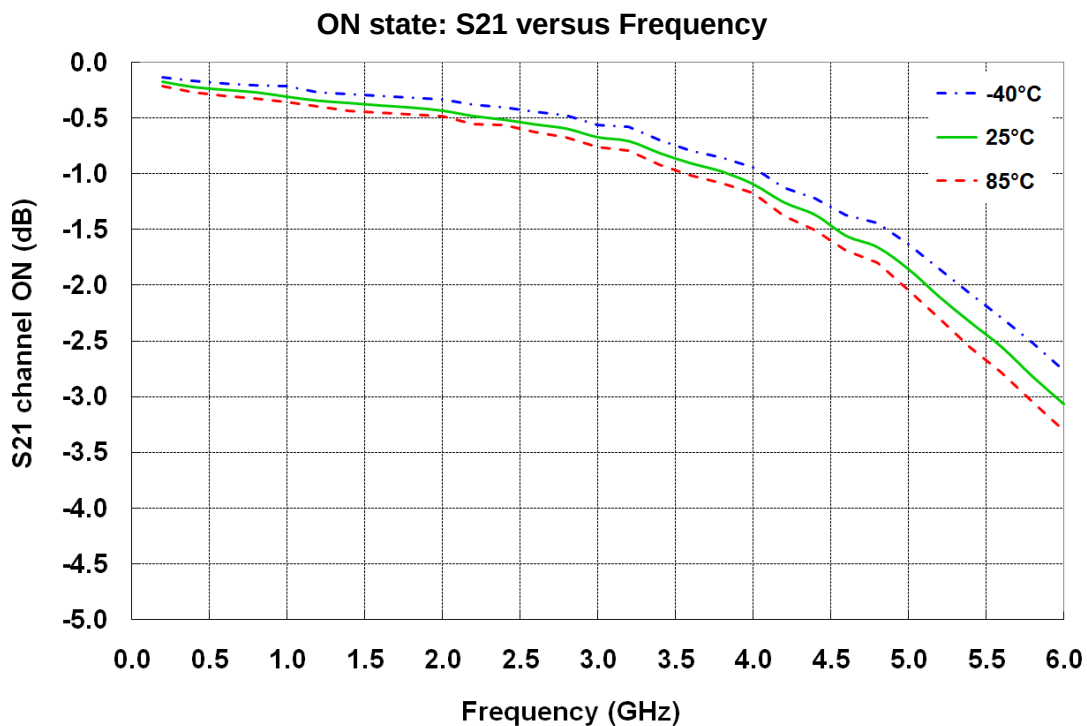


6.4

## Typical Board Measurements

Tamb.= +25°C, VH=0V / VL=-5V

Note: board losses are corrected

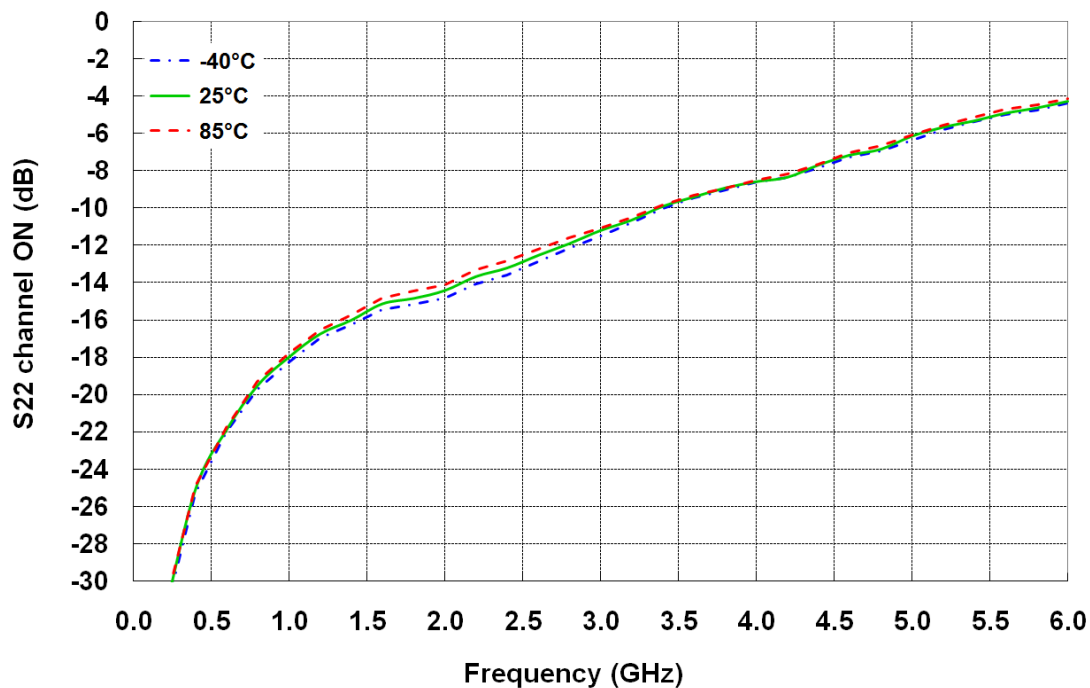


## Typical Board Measurements

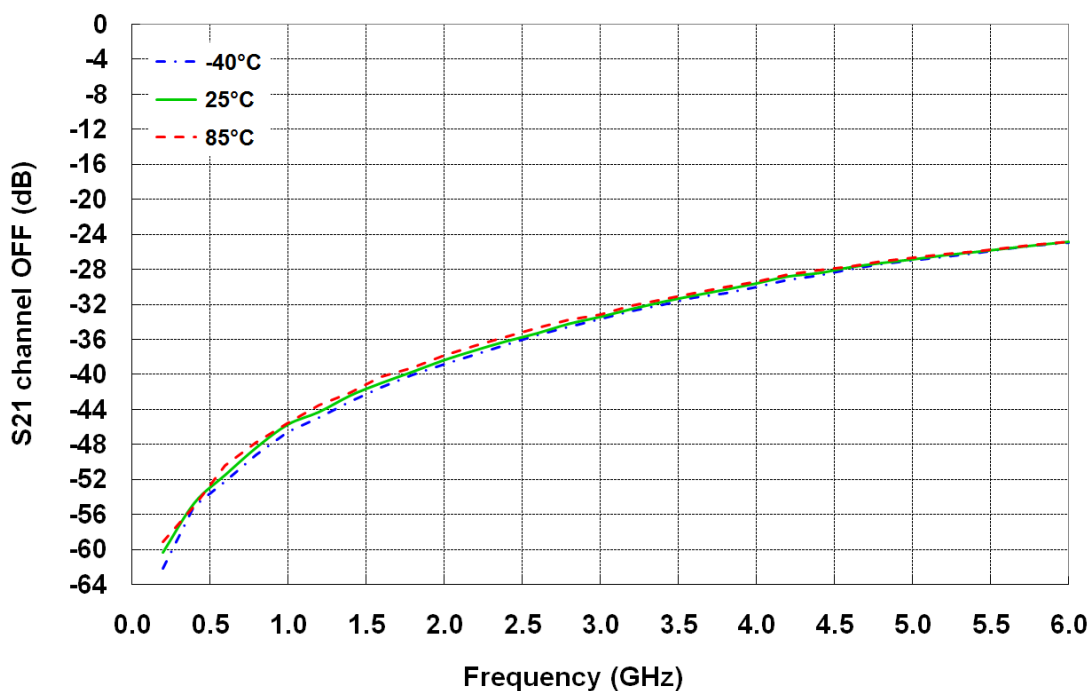
Tamb.= +25°C, VH=0V / VL=-5V

Note: board losses are corrected

ON state: S22 versus Frequency



OFF state: S21 versus frequency

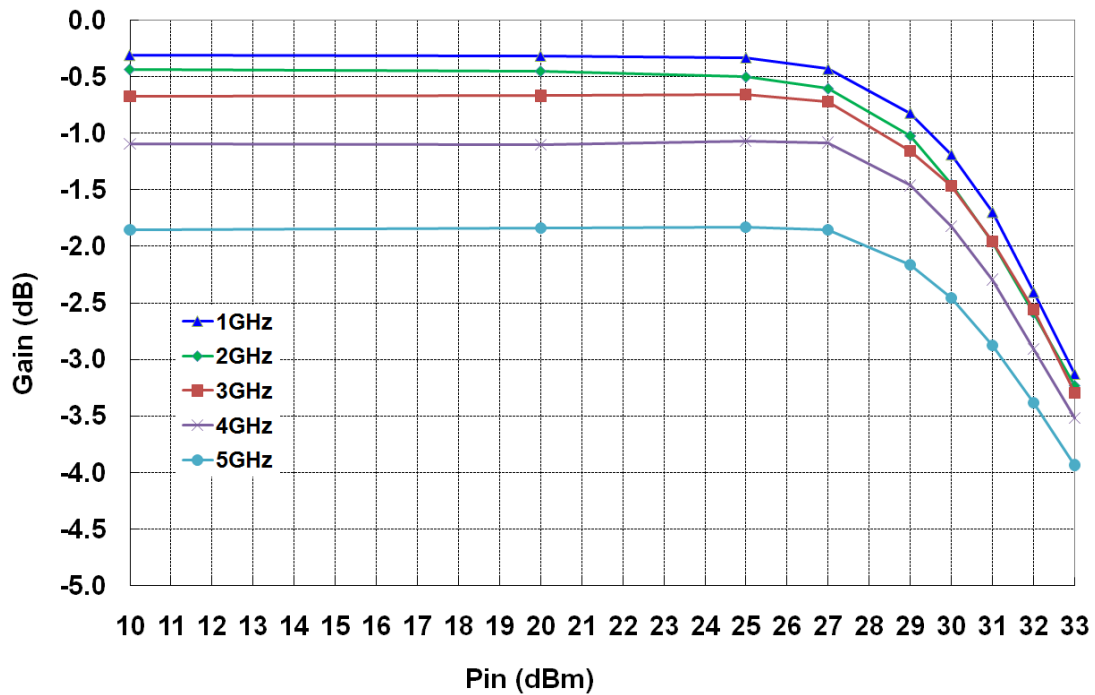


## Typical Board Measurements

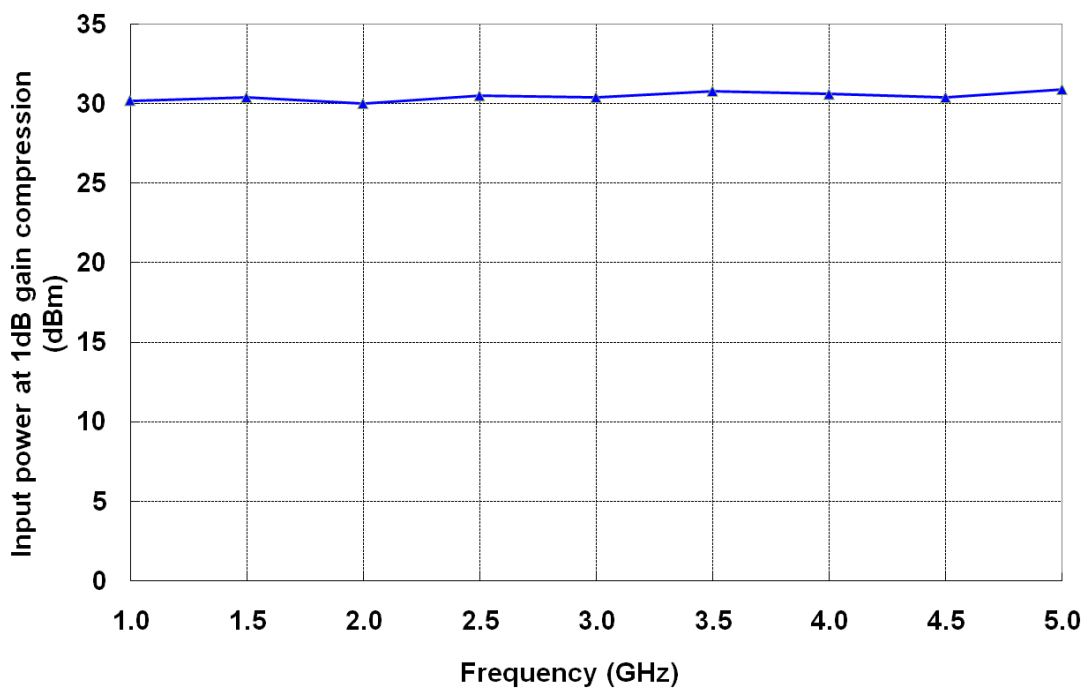
Tamb.= +25°C, VH=0V / VL=-5V

Note: board losses are corrected

Insertion Loss variation versus input power



Input power at 1dB gain compression versus frequency

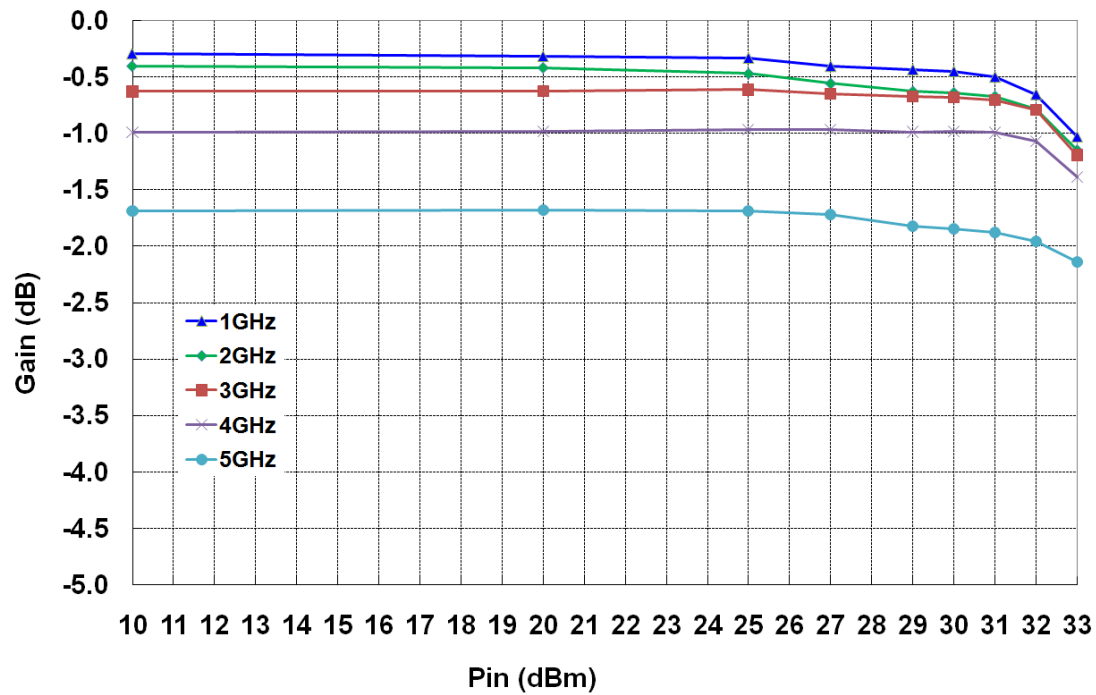


## Typical Board Measurements

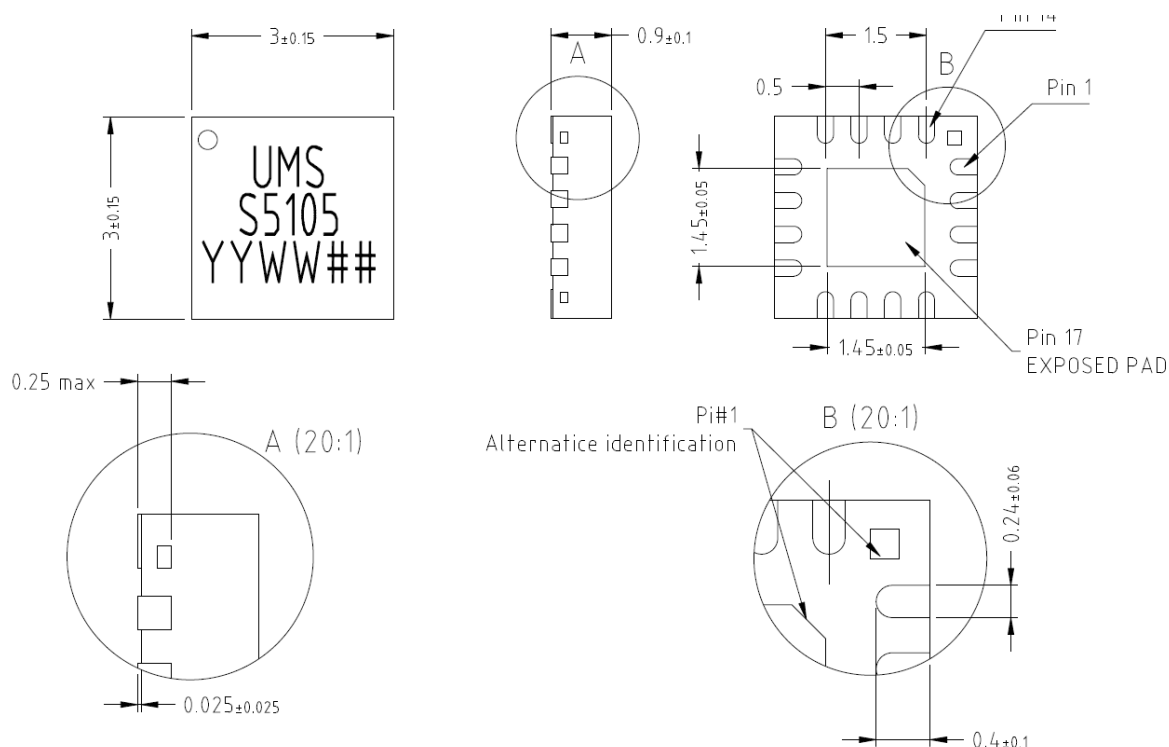
T<sub>amb</sub>. = +25°C, V<sub>H</sub>=0V / V<sub>L</sub>=-8V

Note: board losses are corrected

Insertion Loss variation versus input power





**Package outline <sup>(1)</sup>**

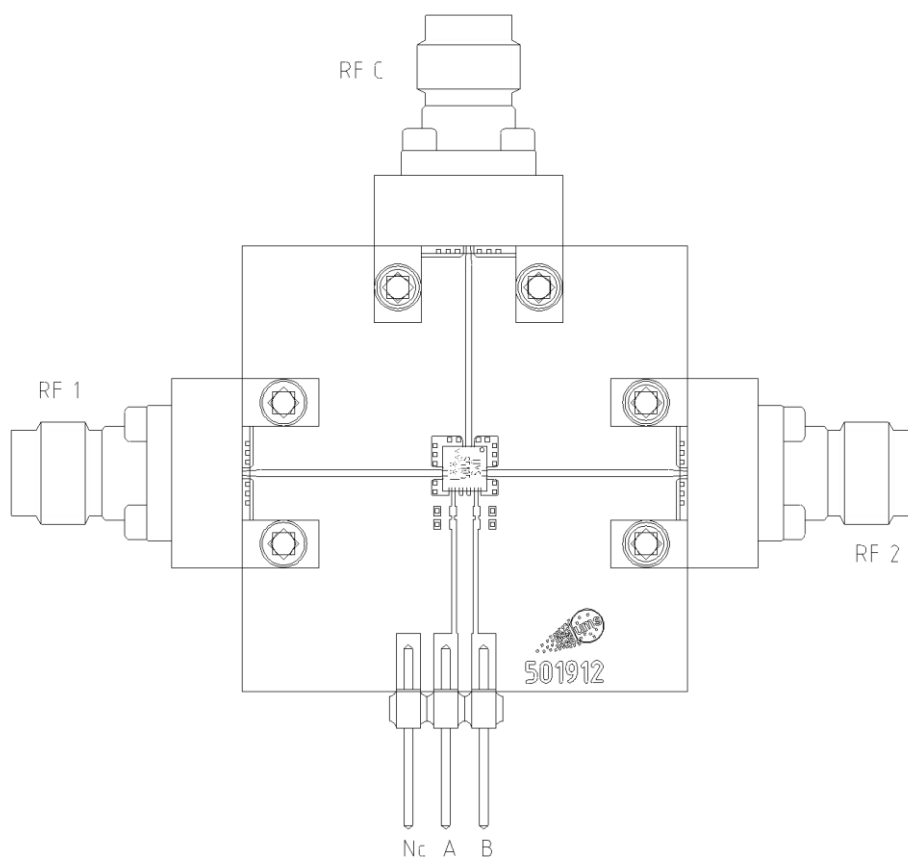
|                     |              |                       |                        |
|---------------------|--------------|-----------------------|------------------------|
| Matt tin, Lead Free | (Green)      | 1- Gnd <sup>(2)</sup> | 9- A                   |
| Units :             | mm           | 2- RFC                | 10- Nc                 |
| From the standard : | JEDEC MO-220 | 3- Gnd <sup>(2)</sup> | 11- Nc                 |
|                     | (VGGD)       | 4- Nc                 | 12- B                  |
|                     | 17- GND      | 5- Nc                 | 13- Nc                 |
|                     |              | 6- Gnd <sup>(2)</sup> | 14- RF2                |
|                     |              | 7- RF1                | 15- Gnd <sup>(2)</sup> |
|                     |              | 8- Nc                 | 16- Nc                 |

<sup>(1)</sup> The package outline drawing included to this data-sheet is given for indication. Refer to the application note AN0017 (<https://www.ums-rf.com>) for exact package dimensions.

<sup>(2)</sup> It is strongly recommended to ground all pins marked "Gnd" through the PCB board. Ensure that the PCB board is designed to provide the best possible ground to the package.

## Evaluation mother board

- Based on typically Ro4003 / 8mils or equivalent.
- Using a micro-strip to coplanar transition to access the package.
- Recommended for implementation of this product on a module board.
- See application note AN0017 for details.



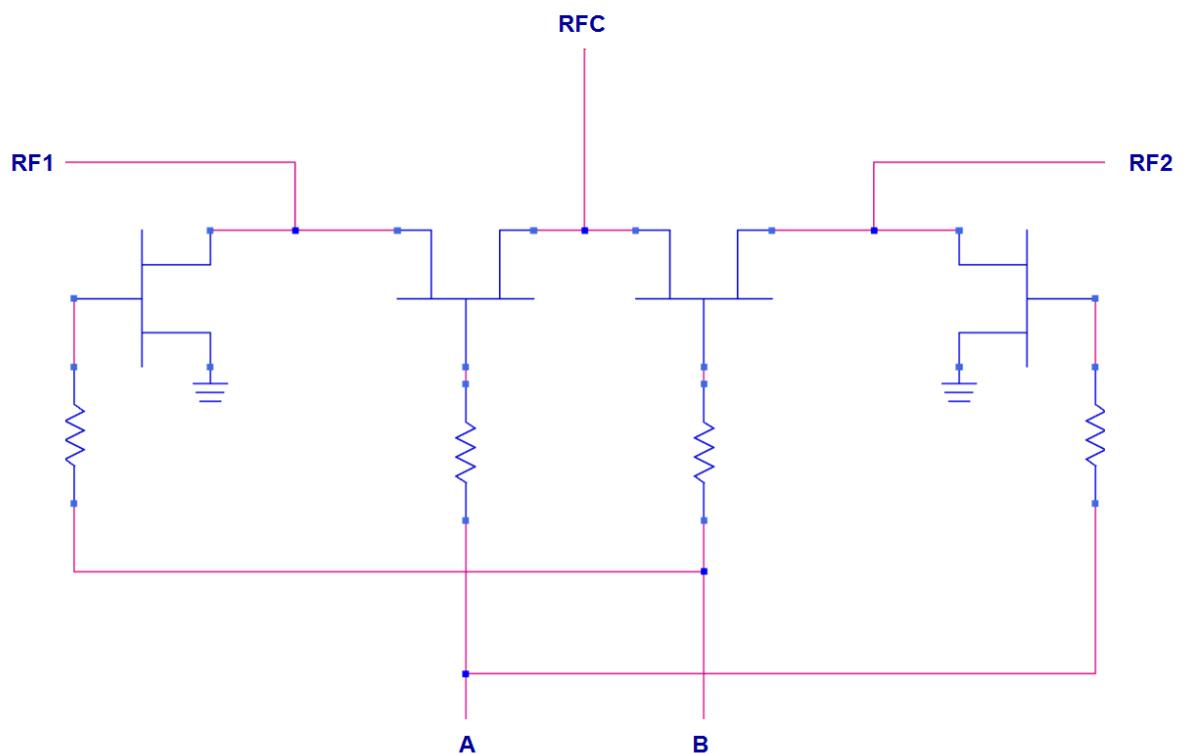
## Recommendation on decoupling

| Label         | Type            | Decoupling                                             | Comment                 |
|---------------|-----------------|--------------------------------------------------------|-------------------------|
| A, B          | Control voltage | Not required                                           | SPDT switch pad control |
| RFC, RF1, RF2 | RF access       | External DC block must be used to ensure DC decoupling | The MMIC is DC coupled  |

## Notes

The DC connections do not include any decoupling capacitor in package; therefore it might be necessary to provide a good external DC decoupling on the PC board, as close as possible to the package.

## DC Schematic



## Recommended package footprint

Refer to the application note AN0017 available at <https://www.ums-rf.com> for package footprint recommendations.

## SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017.

## Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com>.

## Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com> for ESD sensitivity and handling recommendations for the UMS package products.

## Ordering Information

QFN 3x3 package:

CHS5105-QAG/XY

Stick: XY = 20

Tape & reel: XY = 21

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